



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Yoshitaka SASAKI

Application No.: 09/812,553

Filed: March 21, 2001

For: METHOD OF MANUFACTURING THIN FILM MAGNETIC HEAD

RECEIVED  
APR 11 2003  
GROUP 1700

Group Art Unit: 1763

Examiner: R. Culbert

Docket No.: 108972

#5A  
4/14/03  
MLW

AMENDMENT UNDER 37 C.F.R. §1.111

Director of the U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

In reply to the January 16, 2003 Office Action, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 34, line 15 to page 35, line 12, delete current paragraph and insert therefor:

A<sub>1</sub>

By selectively etching and patterning the top pole tip precursor layer 112a by RIE with the first mask 22a, as shown in Figs. 7A and 7B and Fig. 16, the top pole tip 12a made of iron nitride is selectively formed in a part of the area on the write gap layer 11 and a part of the area on the insulating film pattern 10. By the etching process, the area (except for the portion which becomes the magnetic path connection portion 12b) other than the area of forming the first mask 22a in the top pole tip precursor layer 112a (which is not shown in Figs. 7A and 7B and Fig. 16) is selectively removed. At the time of forming the top pole tip 12a, simultaneously, the another mask 22b is used and the magnetic path connection portion 12b (not shown in Fig. 16) is formed in the opening 10k. The top pole tip 12a and the magnetic path connection portion 12b construct a part of the top pole 12. The top pole tip